

said emitter region and said stop zone having mutually opposite conductivities; and

said stop zone having atoms of a doping substance determining a conductivity of said stop zone, said atoms of said doping substance having at least one energy level within the band gap of the semiconductor and at least 200 meV away from both a conduction band and a valence band of the semiconductor.

Enter The Following New Claims:

-- 4. A power semiconductor element, comprising:

an emitter region;

a stop zone in front of the emitter region;

said emitter region and said stop zone having mutually opposite conductivities; and

said stop zone containing foreign atoms selected from the group consisting of sulfur and selenium with at least one energy level within the band gap of the semiconductor and spaced at least 200 meV from a conduction band and a valence band of the semiconductor. --